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N-Channel SuperFET[®] FRFET[®] MOSFET 600 V, 20 A, 190 mΩ

Features

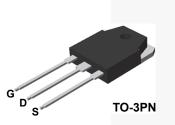
- 650 V @ T_J = 150°C
- Typ. R_{DS(on)} = 150 mΩ
- Fast Recovery Type (Typ. T_{rr} = 160 ns)
- Ultra Low Gate Charge (Typ. Q_g = 75 nC)
- Low Effective Output Capacitance (Typ. Coss(eff.) = 165 pF)
- 100% Avalanche Tested
- RoHS Compliant

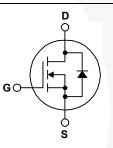
Applications

- LCD / LED / PDP TV
- Solar Inverter
- AC-DC Power Supply

Description

SuperFET[®] MOSFET is Fairchild Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications. SuperFET FRFET[®] MOSFET's optimized body diode reverse recovery performance can remove additional component and improve system reliability.





Absolute Maximum Ratings Tc = 25°C unless otherwise noted.

Symbol	Parameter		FCA20N60F	Unit	
V _{DSS}	Drain-Source Voltage		600	V	
ID	Drain Current - Continuous (T _C = 25 - Continuous (T _C = 10		20 12.5	A A	
I _{DM}	Drain Current - Pulsed	(Note 1)	60	A	
V _{GSS}	Gate-Source voltage		± 30	V	
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	690	mJ	
I _{AR}	Avalanche Current	(Note 1)	20	A	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	20.8	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	50	V/ns	
P _D	Power Dissipation (T _C = 25°C) - Derate . bove 25°C		208 1.67	W W/°C	
T _{J,} T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C	
Τ _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C	

Thermal Characteristics

Symbol	Parameter	FCA20N60F	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.6	°C/W	
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

May 2014

Part Number Top Ma		Top Mark	Package	Packing Method	Reel Size	Ta	pe Width	ו Qu	antity	
FCA20	FCA20N60F FCA20N60F		TO-3PN	TO-3PN Tube N/A		N/A		30	30 units	
=lectric:	al Chara	acteristics T - 200	C uploss otherwi	a noted						
Symbol	ectrical Characteristics T _C = 25°C unle mbol Parameter			Conditions		Min.	Тур.	Max.	Unit	
Off Charac	teristics								<u> </u>	
BV _{DSS}	Drain-Sour	ce Breakdown Voltage	V _{GS} =	V _{GS} = 0 V, I _D = 250 μA, T _J = 25°C					V	
			V _{GS} =	$V_{GS} = 0 V, I_D = 250 \mu A, T_J = 150^{\circ}C$			650		V	
ΔΒV _{DSS} / ΔΤ _J	Breakdown Voltage Temperature Coefficient		I _D = 28	$I_D = 250 \ \mu$ A, Referenced to 25°C			0.6		V/°C	
BV _{DSS}	Drain-Sour Voltage	ce Avalanche Breakdow	anche Breakdown $V_{GS} = 0 V, I_D = 20 A$			700		V		
I _{DSS}	Zero Gate Voltage Drain Current			$V_{DS} = 600 V, V_{GS} = 0 V,$ $V_{DS} = 480 V, T_{C} = 125^{\circ}C$				10 100	μΑ μΑ	
I _{GSSF}	Gate-Body	Leakage Current, Forwa	ard V _{GS} =	30 V, V _{DS} = 0V				100	nA	
I _{GSSR}	Gate-Body	Leakage Current, Reve	rse V _{GS} =	-30 V, V _{DS} = 0V				-100	nA	
On Charac	teristics									
V _{GS(th)}	Gate Threshold Voltage $V_{DS} = V_{GS}, I_D =$		V _{GS} , I _D = 250 μA		3.0		5.0	V		
R _{DS(on)}	Static Drain-Source On-Resistance		V _{GS} =	V _{GS} = 10 V, I _D = 10 A			0.15	0.19	Ω	
9 _{FS}	Forward Tr	ransconductance	V_{DS} =	40 V, I _D = 10 A			17		S	
Dynamic C	haracterist	ics								
C _{iss}	Input Capa	citance		$V_{DS} = 25 V, V_{GS} = 0 V,$ f = 1.0 MHz			2370	3080	pF	
C _{oss}	Output Ca	pacitance	f = 1.0				1280	1665	pF	
C _{rss}	Reverse T	ransfer Capacitance					95		pF	
C _{oss}	Output Ca	pacitance	V _{DS} =	V_{DS} = 480 V, V_{GS} = 0 V, f = 1.0 MHz			65	85	pF	
C _{oss} eff.	Effective Output Capacitance		V _{DS} =	V_{DS} = 0 V to 400 V, V_{GS} = 0 V			165		pF	
Switching	Characteris	tics								
t _{d(on)}	Turn-On D	elay Time		$\label{eq:VDD} \begin{array}{c} V_{DD} = 300 \text{ V}, \text{ I}_{D} = 20 \text{ A}, \\ R_{G} = 25 \Omega \end{array}$			62	135	ns	
t _r	Turn-On R	ise Time	R _G = 2				140	290	ns	
t _{d(off)}	Turn-Off D	elay Time					230	470	ns	
t _f	Turn-Off Fa	all Time					65	140	ns	
Qg	Total Gate	Charge		$V_{DS} = 480 \text{ V}, \text{ I}_{D} = 20 \text{ A},$ $V_{GS} = 10 \text{ V}$ (Note 4)			75	98	nC	
Q _{gs}	Gate-Sour	ce Charge	V _{GS} =				13.5	18	nC	
Q _{gd}	Gate-Drain	Charge					36		nC	
Drain-Sour	ce Diode C	haracteristics and Max	imum Rating	IS				1	<u> </u>	
I _S	Maximum Continuous Drain-Source Diode Forward Current					20	Α			
I _{SM}	Maximum	Pulsed Drain-Source Dic	de Forward (Current				60	А	
V _{SD}	Drain-Sour	ce Diode Forward Voltag	ge V _{GS} =	0 V, I _S = 20 A				1.4	V	
t _{rr}		ecovery Time	V _{GS} =	$V_{GS} = 0 V, I_{S} = 20 A,$ dI _F /dt = 100 A/µs			160		ns	
Q _{rr}		ecovery Charge	dl _F /dt				1.1		μC	

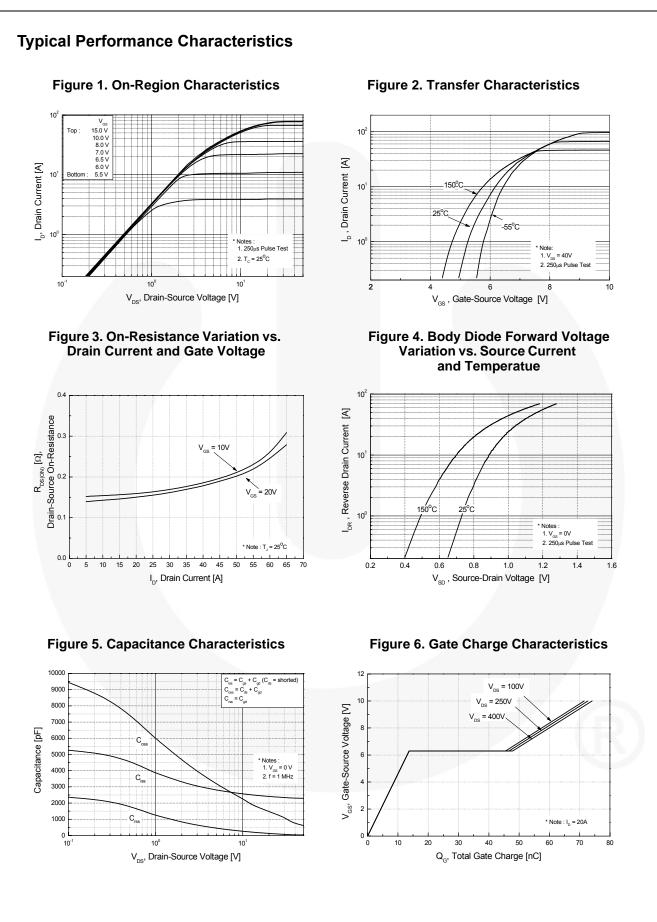
1. Repetitive rating: pulse-width limited by maximum junction temperature.

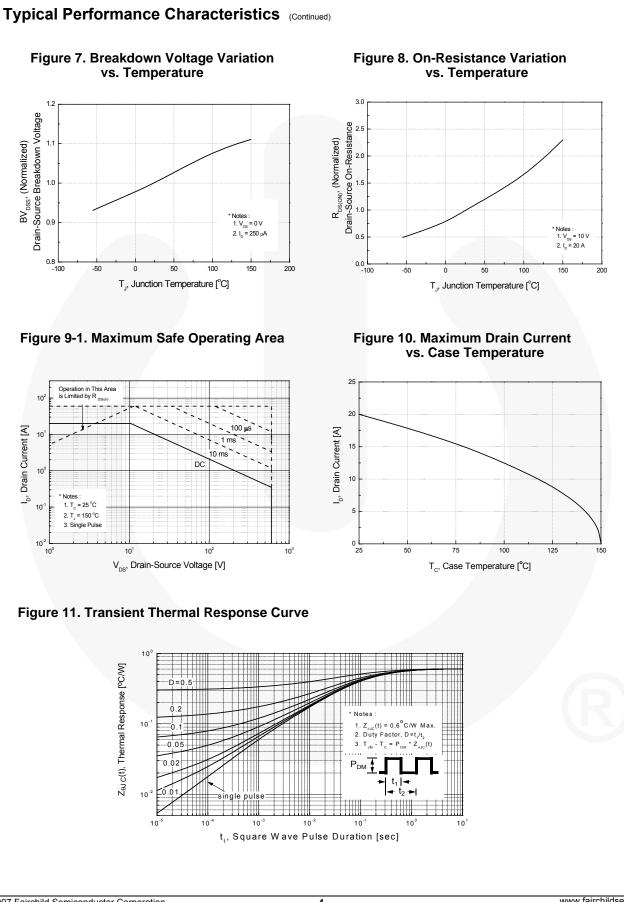
2. I_{AS} = 10 A, V_{DD} = 50 V, R_{G} = 25 $\Omega,$ starting T_{J} = 25°C.

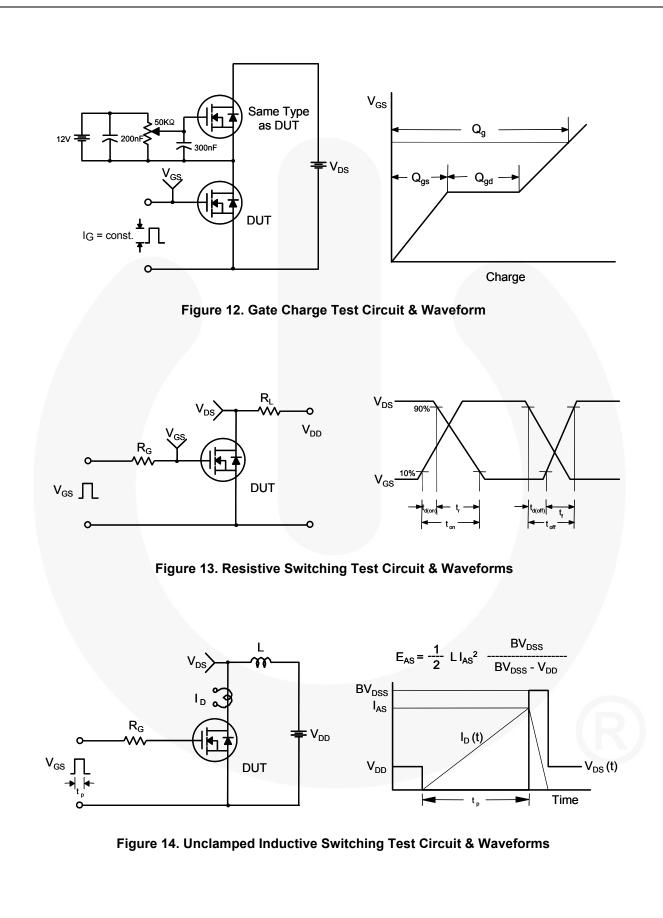
3. $I_{SD} \le 20$ A, di/dt ≤ 1200 A/µs, $V_{DD} \le BV_{DSS}$, starting T_J = 25°C.

4. Essentially independent of operating temperature typical characteristics.

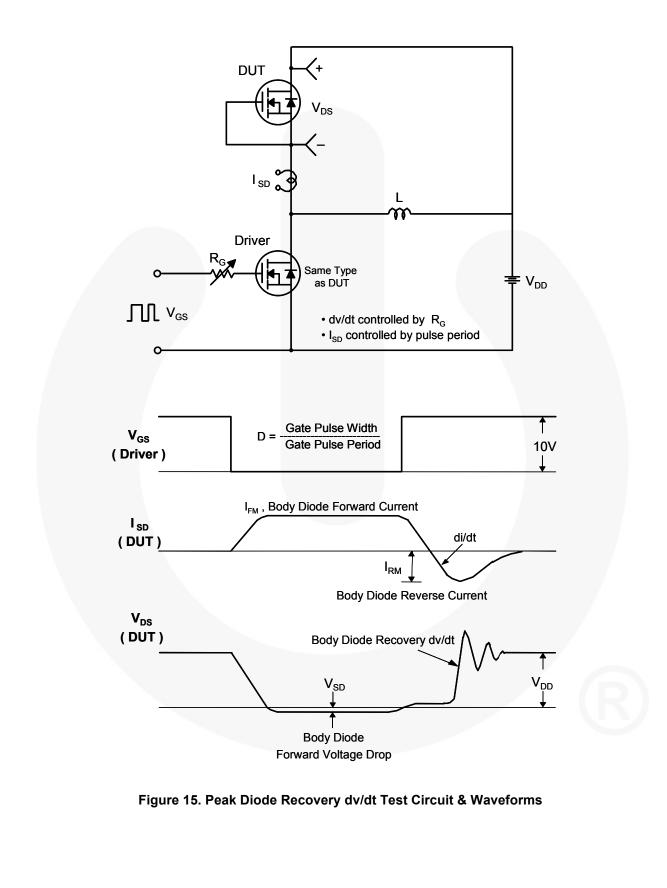
FCA20N60F — N-Channel SuperFET[®] FRFET[®] MOSFET



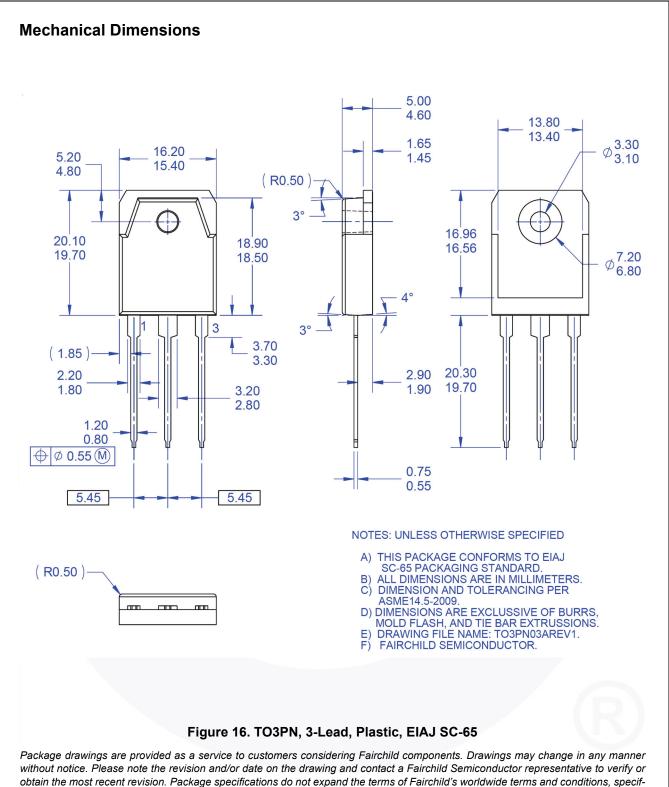




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